intel®

AP-610

APPLICATION NOTE

Flash Memory In-System Code and Data Update Techniques

BRIAN DIPERT
SENIOR TECHNICAL
MARKETING ENGINEER

February 1995

Order Number: 292163-002

Additional copies of this document or other Intel literature may be obtained from:

Intel Corporation
Literature Sales
P.O. Box 7641
Mt. Prospect, IL 60056-7641

or call 1-800-879-4683

CG-041493

1.0 INTRODUCTION

The ability to update flash memory contents with the system operational distinguishes flash memory from other nonvolatile technologies such as ROM and EPROM. This capability is key for using flash memory in a wide range of applications:

- Code storage/execution (code DRAM and ROM replacement),
- Data storage (EEPROM, battery RAM emulation, etc.), and
- File storage (flash-based solid state drive)

System software implementations for in-system code and data update must comprehend algorithm execution during flash memory program/erase. Implementations also vary according to the level of system code/data access required during update.

This application note discusses these topics and gives general recommendations that can be tailored to specific system needs. It focuses on Intel's Boot Block, FlashFile™ and Embedded Flash RAM memories which have on-chip program/erase automation and block erasure. However, many of the concepts can be equally applied to Intel's bulk erase flash memories.

2.0 GENERAL INFORMATION

Definition of Terms

Design engineers can select from up to three unique approaches to update stored flash memory information. Before proceeding, let's define these terms to make it clear what we will and won't be discussing in this application note:

1. *In-System Write (ISW):* As first described earlier, during an in-system update the system is powered up and either partially or fully operational. The system CPU (see Figure 1) executes the flash memory program/erase algorithms and obtains new code/data from one of several sources (serial or parallel port, floppy or hard disk drive, modem, etc.).

2. *On-Board Programming (OBP):* In this approach, the flash memory is also installed on the system board. However, OBP does not use the system CPU and, in fact, commonly powers down the processor or holds it in a HALT mode. The flash memory connects to an off-board "computer" such as a board tester or prom programmer. This off-board intelligence provides the necessary commands and data to erase and reprogram the flash memory. This technique is covered in other documentation available from Intel Corporation. See the Additional Information section of this application note.

3. *PROM Programming:* This approach was first made popular back in the days of PROMs and EPROMs. The flash memory is initially programmed, and is reprogrammed, by removing it from the system board and socketing it in dedicated hardware called a PROM programmer. Intel works closely with a wide range of PROM programmer vendors to ensure support for all of its flash memory products. See the Additional Information section of this application note for details.

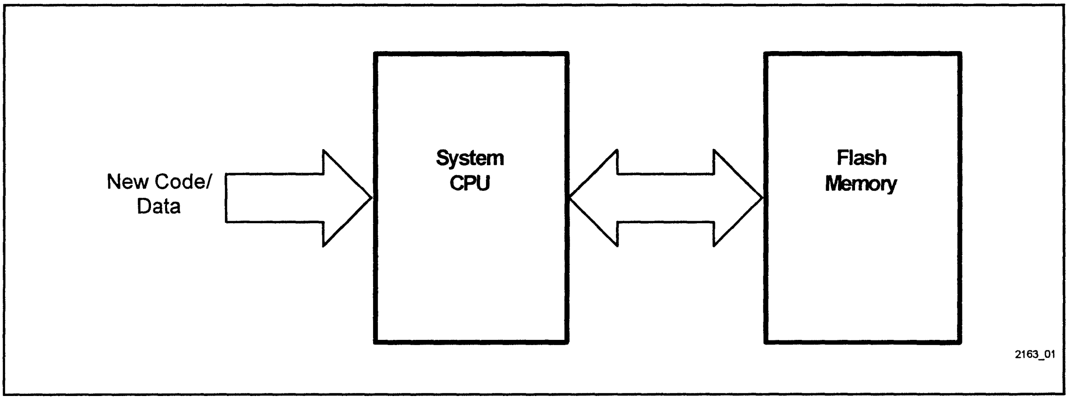

Figure 1. The System CPU Controls the In-System-Write Flash Memory Update

Read-While-Write

The fundamental concept to understand when considering in-system updates is that of read-while-write. Stated simply, it is currently NOT possible with any of today's flash memory technology alternatives to read from the flash memory array while simultaneously programming or erasing it. There are several basic reasons for this:

a. During program or erase, the flash memory row and column decode architecture results in high voltages present throughout the array. Isolating these voltages to a specific byte/word or block would have excessive die size and (therefore) silicon cost impacts given that inexpensive system implementation alternatives exist. Keep reading for details!

b. Intel's Boot Block, FlashFile and Embedded Flash RAM memories all have on-chip program/erase automation. After these flash memories receive program or erase command sequences, they automatically transition to a mode where they provide status register information (versus array or other data). This transition quickly provides the system with the information it needs to determine program/erase status, minimizing system software overhead and maximizing effective write/erase performance.

Flash memory array reads (to access code or data) CAN take place at any time that the flash memory automation is READY (either completed or suspended). Figure 2 gives a simple flash memory update algorithm example. It shows portions of the code that must be executed off-chip, and shaded areas show "windows" where the flash memory array can be accessed, if needed, by writing the Read Array command and then reading from desired locations. These "windows" will be described in detail in Section 4.0. Thanks to on-chip automation, the amount of code executed off-chip to actually program/erase the flash memory is very small. Overhead needed to obtain new code/data from the system varies with the method chosen.

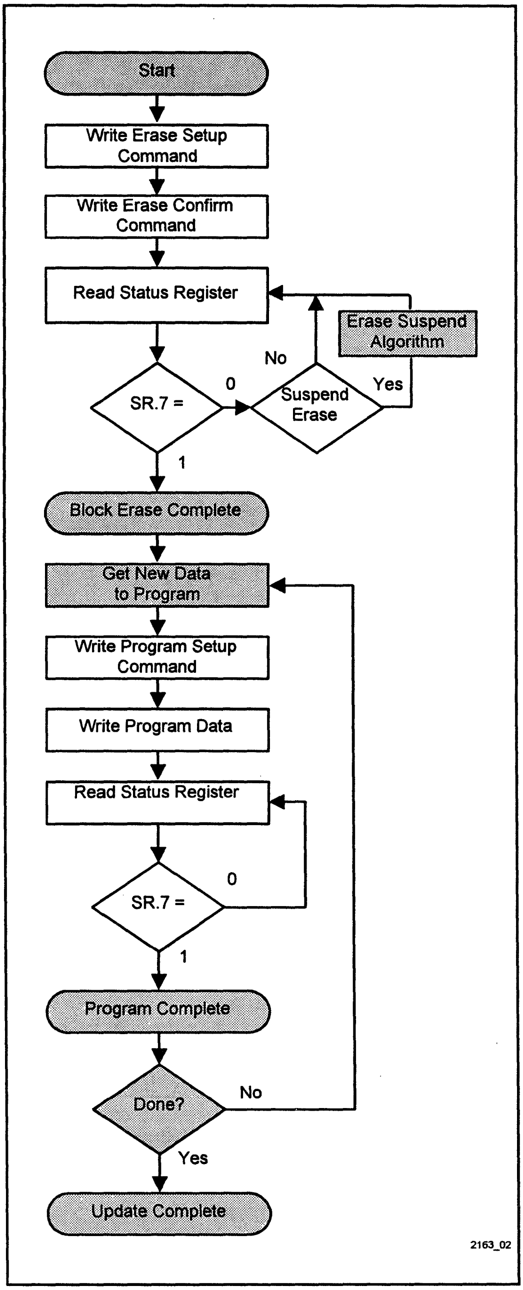

Figure 2. Simple Code/Data Block Update Algorithm Shows Shaded "Window" Opportunities for Array Reads

What Amount of System Functionality Is Needed During Update?

The answer to the above question is key to understanding the amount of software architecting needed to integrate flash memory into your design. Use the following question as a reference for where to continue reading:

Q. Can you dedicate the system exclusively to the flash memory update and ignore all other non-related interrupts? Said another way, can you take the system "off-line" during flash memory updates?

A_1. If your answer is "yes," the software implementation is very straightforward. See Sections 3.0 and 5.0.

A_2. If your answer is "no," the specific software implementation varies. One approach uses redundant system memory to separate the execution and storage/backup regions. Another technique eliminates this redundancy but depends on an understanding of interrupt latency, interrupt frequency and its variability with time. See Sections 4.0 and 5.0.

Dedicated Blocks for System Boot Code: Recovery from System Power Loss or Reset during Flash Memory Update

Several of the approaches described in Sections 3.0 and 4.0 that follow use system RAM to execute the flash memory update algorithms. This brings up a logical question; what happens if the system resets or loses power in the middle of a flash memory update? In this case, system RAM contents will be invalid, including the flash memory update code. The byte being programmed or the block being erased when system reset/power loss occurs will be left in an indeterminate state and will need to be reprogrammed/erased.

Flash memory's blocked architecture provides protection for system boot code and enables the system to recover fully from incomplete code updates. All boot block components as well as 16-/32-Mbit FlashFile and embedded flash RAM memories also allow hardware "lock" of boot code for additional protection. This boot code, after minimally initializing system hardware, should execute a checksum verify of the remainder of the flash memory. If this checksum "passes," system boot can continue. If a checksum "fail" is obtained, this reflects an incomplete program or erase, and the system should alert the user and execute a repeat update. Figure 3 flowcharts this algorithm.

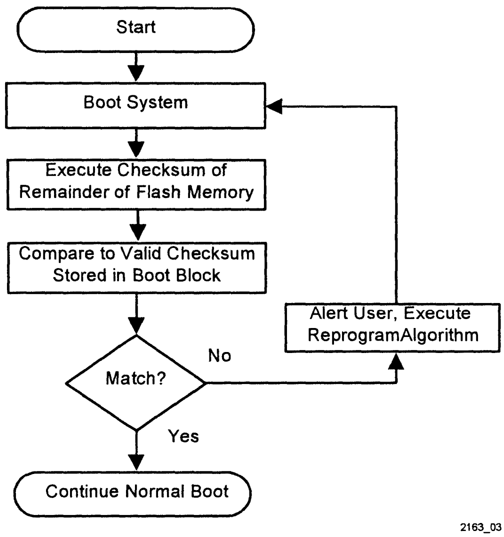

Figure 3. Checksum Validation Confirms Flash Memory Integrity

Intel's 16-/32-Mbit FlashFile and embedded flash RAM memories indicate via Status Register feedback whether an erase in progress has been aborted by power loss or hardware power-down. The 16-Mbit Flash Product Family User's Manual covers this topic in detail. See the Additional Information section of this application note.

3.0 "OFF-LINE" FLASH MEMORY UPDATES

Reviewing the Q-and-A discussion earlier, you should be reading this section if you can ensure that the system will receive no interrupts that will require flash memory array access during the update process. Examples of this scenario are numerous:

- Cellular phones that are placed in a special "maintenance" mode for updates.
- PC BIOS applications where the user runs a dedicated "update" routine to upgrade the resident flash memory code.
- Laser printers that can be taken "off-line" prior to the update process.
- Many other applications. . . .

Again referencing Figure 2, we see that the shaded areas of the algorithm can be ignored since flash memory array access is not needed until after the update is complete. The resultant algorithm, shown in Figure 4, is small in size and straightforward in implementation. It can be stored within one of the flash memory blocks if desired, and is copied to/executed from an external memory. Scenarios that follow show two of the many possible implementation options.

Technique 3.1: Algorithm Execution from RAM

The RAM in this technique can be located in several different places within the system, such as:

- In a discrete SRAM or DRAM chip
- Integrated within an embedded microprocessor or microcontroller
- Integrated within a system ASIC
- In a Page Buffer of a separate 16-Mbit FlashFile memory

An important requirement is that the system be able to execute code (not just read and write data) out of the RAM. Ideally, to minimize system overhead and maximize effective update throughput, the update algorithm should be present in RAM at all times during system operation. If this is not possible due to "RAM crunch," the up-front time required to upload the algorithm to RAM must be factored into system update performance calculations.

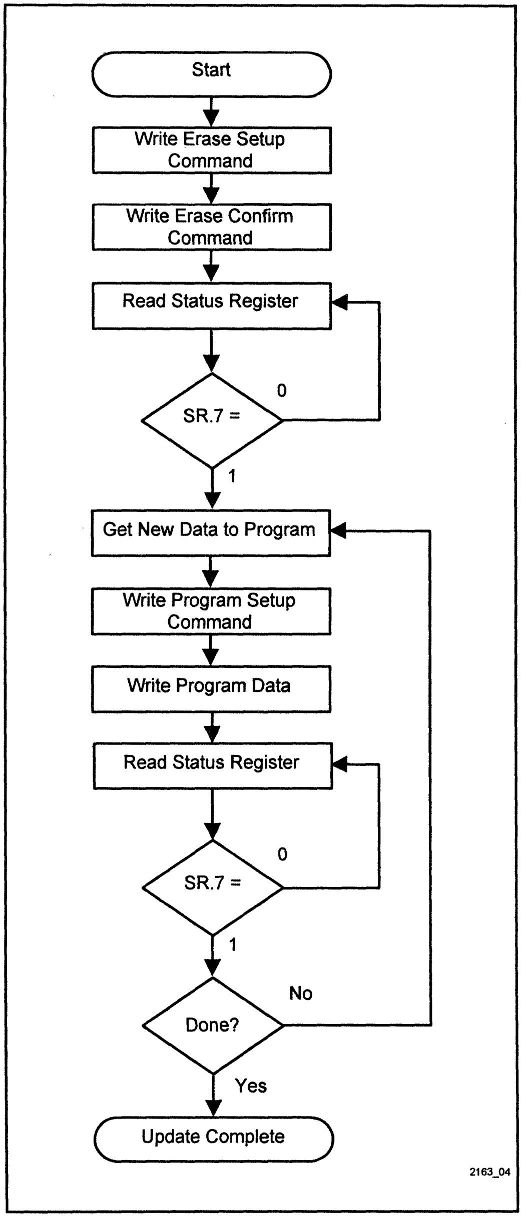

Figure 4. The Block Erase/Program Algorithm Is Simplified for "Offline" Updates

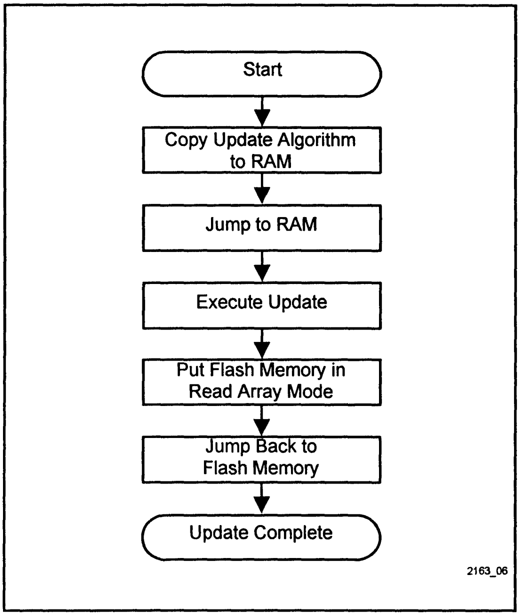

Figure 5. Executing the Update Algorithm Requires Minimal System RAM

Figure 5 shows the overall flowchart used when executing the update algorithm out of system RAM. As mentioned earlier, flash memory automation means that the amount of code executed off-chip to actually program/erase the flash memory is very small. Overhead needed to obtain new code/data from the system varies with the method chosen (diskette, modem, serial or parallel port, etc.).

Does your system include at least one 16-/32-Mbit FlashFile memory and other flash memories? If so, you can potentially use the 256 byte page buffer of the FlashFile memory as the execution RAM while updating the other flash memories! Note: it is NOT possible to completely execute an update algorithm from the page buffer of a flash memory while simultaneously updating that same memory.

Technique 3.2: Algorithm Execution from Nonvolatile Memory

If the system contains multiple flash memories, implementation is very straightforward. Store a duplicate copy of the update code in each flash memory, and execute from one device while updating the other(s). Figure 6 gives one example, using two Intel 28F001BX Boot Block flash memories.

This same technique can be applied to any other nonvolatile memory in the system. Examples include boot ROM, ROM locations within an ASIC or nonvolatile memory integrated within an embedded microprocessor or microcontroller.

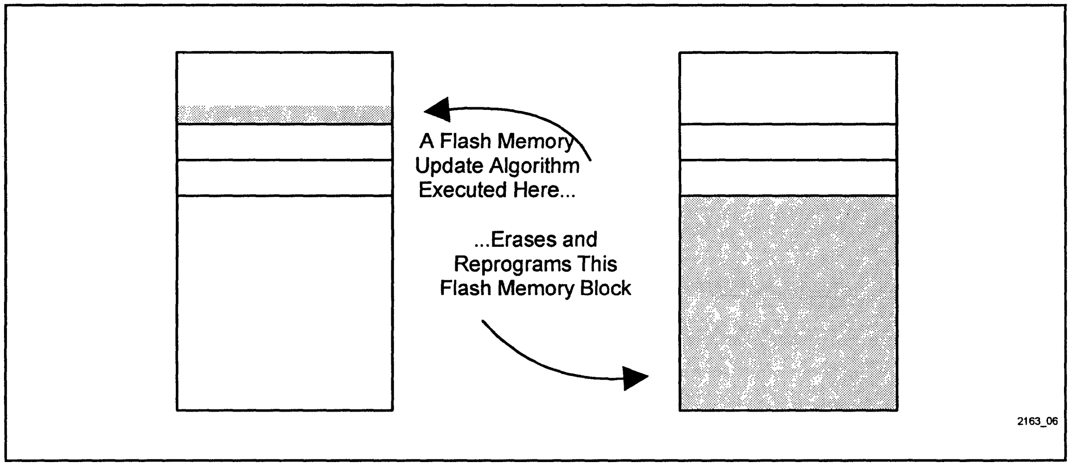

Figure 6. Executing the Flash Memory Update Algorithm from Another Nonvolatile Memory Requires No Dedicated RAM

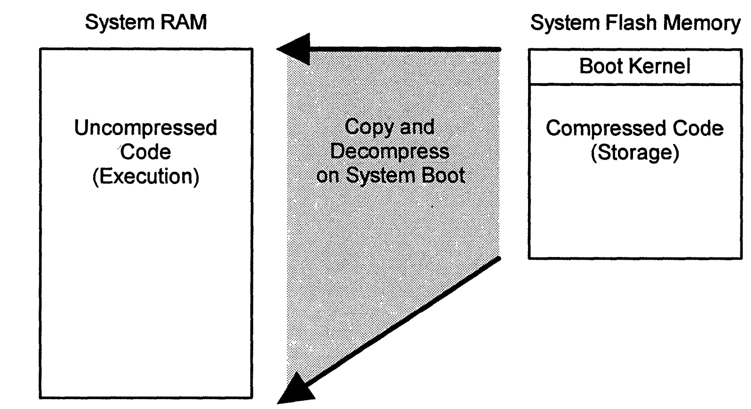

Figure 7. Redundant System RAM Enables Access to All Code during Flash Memory Update

4.0 "ON-LINE" FLASH MEMORY UPDATES

Reviewing the Q-and-A discussion earlier, you should be reading this section if the system must be partially or fully operational during the flash memory update process. Said another way, it must be able to detect and service some or all possible system interrupts. Examples of this scenario include:

- Cellular base stations that must be able to service incoming connection requests.
- Data Communications router and hub networks that cannot be taken off-line.
- Telecommunications PBX switch networks that must be always-operational.

Technique 4.1: Code Redundancy in System RAM

This system memory configuration, shown in Figure 7, is relatively common today in high-performance systems. The system boots from flash memory, copies code to code DRAM (sometimes decompressing in the process) and jumps to DRAM for execution. DRAM is used here primarily because of its high-performance reads.

In this case, the system has access to all interrupt service routines during the flash memory update process. After update is complete, a quick system "reset" will reboot the system and load DRAM with the new code. The amount of time that the system cannot service interrupts is the combination of system reboot and copy-to-DRAM delays.

Technique 4.2: Code Redundancy in System Flash Memory

Figure 8 gives an example of this system memory configuration. Two banks of flash memory components store "previous" and "latest" versions of system code. The system executes from one bank while updating the other bank. Once update successfully completes, an address or control signal "toggle" swaps the "previous" and "latest" banks and enables immediate execution of the latest software version.

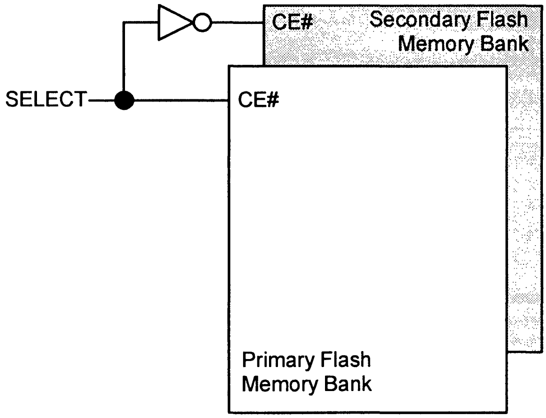

Figure 8. Dual Flash Memory Banks Eliminate RAM Reload Delays

The obvious advantage of this approach include constant access to all interrupt service routines and a non-existent reboot delay. Memory redundancy will incur additional system cost, which must be balanced against advantages and compared to total system cost (and price) to determine applicability of this approach.

Technique 4.3: Leveraging Flash Memory Automation: Programming Performance and Erase Suspend Latency

This approach eliminates both the redundancy of multiple memories and the reboot delay of the flash/DRAM solution in Technique 4.1. It is especially attractive for use with Intel's Embedded Flash RAM memories, whose read performance approaches or exceeds that of DRAM. In this case, the need for redundant code DRAM (for performance reasons) is eliminated.

Before continuing your reading of this section, please do the following research:

- Analyze the latencies of each of your system interrupt routines. Which routines take the longest to execute, and how long do they take?
- Analyze the profile of frequency of interrupts. How often do interrupts occur, and how does this frequency vary with time of day, week, month and year? Can updates be scheduled for times when the interrupt frequency is low (or ideally, zero)?

The flash memory automation approach "hides" byte/word programming operations within the time delay between interrupts. It also "hides" slow block erase by using erase suspend/resume to read from the flash memory when required. Referring back to Figure 2, we see that reads from the flash memory (to access interrupt service routines) can occur at the conclusion of programming, at the conclusion of erase and while erase is suspended. This approach exploits these access "windows."

As an example, we'll construct the following scenario (reference Figure 9).

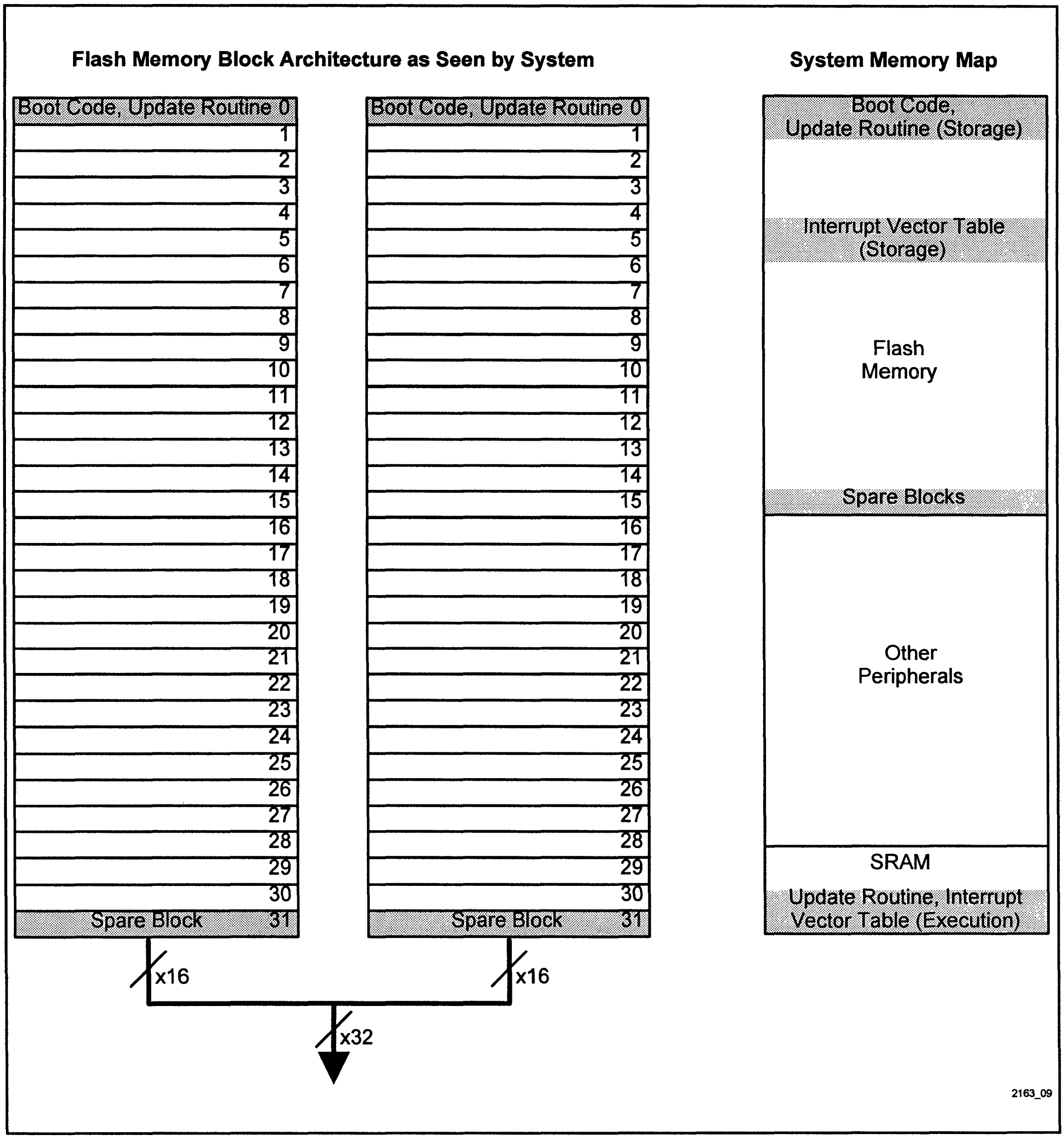

Figure 9. Leveraging Flash Memory Automation Eliminates System Memory Redundancy, Enables Full Interrupt Servicing throughout the Update Process

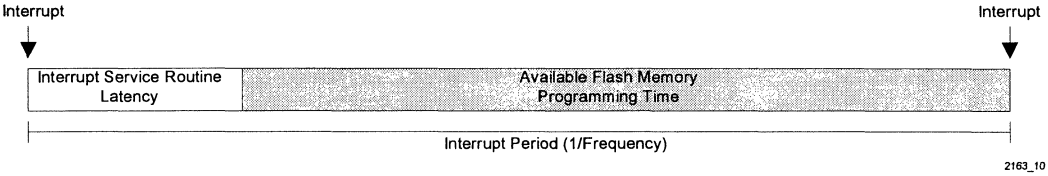

Figure 10. Available Time between System Interrupts Enable Flash Memory Programming

Components

Two 28F016SV flash memories (5V V_{CC}, 12V V_{PP}), each x16, interfacing to a x32 system bus

Small system SRAM

Timings

System interrupt frequency (period) = every 200 µs.

Longest interrupt service routine latency = 50 µs.

Flash memory per-location programming time = 6 µs (typical)

Flash memory erase suspend latency = 10 µs (typical)

Interrupts During Programming

Looking first at programming (Figure 10), we see that the goal is to execute at least one programming operation within the period between interrupts. In the scenario described above, subtracting interrupt service routine latency from interrupt period gives a 150 µs "window" in which programming can occur. At 6 µs per double-word, up to 25 locations can be programmed within each interrupt period.

200 µs (interrupt period) – 50 µs (ISR latency) = 150 µs (programming "window") 150 µs (window)/6 µs (programming time per location) = 25 locations

Intel's 16-/32-Mbit FlashFile memories contain on-chip page buffers, each 256 bytes in size, that dramatically increase effective per-byte programming performance. For example (averaged over a page), typical programming performance for the Intel 28F016SV is 2.1 µs/byte at 5V V_{CC} and 12V V_{PP}. Using these page buffers may, in some cases, allow the system to program even more bytes within each interrupt programming "window."

Interrupts During Erase

Now for erase. If an interrupt occurs during erase, the system must be able to suspend erase, read the flash memory array and service the interrupt, all before the next interrupt. Looking at Figure 11, adding erase suspend latency to interrupt service routine latency and subtracting from interrupt period shows that 140 µs of flash memory erase automation can execute between each interrupt. Obviously, block erase time will extend beyond that specified in the device datasheet since erase is being repeatedly suspended.

200 µs (interrupt period) – [10 µs (erase suspend latency) + 50 µs (ISR latency)] = 140 µs (erase "window")

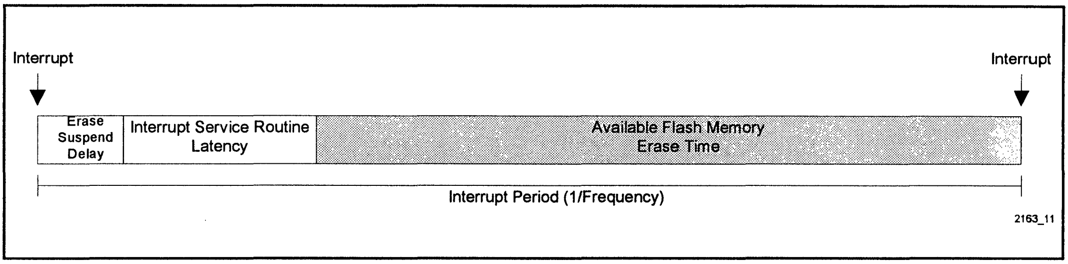

Figure 11. Available Time between System Interrupts Enables Flash Memory Erase, and Erase Suspend Allows Array Access for Interrupt Service Routines

Accessing the Existing Version of Code in a Block Being Updated

All well and good. We've shown how to access code in other flash memory blocks (for example blocks 2–30) while erasing or reprogramming another block (for example, block 1). But what happens if the code you need to read is the code in the process of being updated? Where do you put the previous version of this code?

One approach, shown in Figure 9, assumes that at least one spare block is available in each flash memory (for example, block 31). Before updating any block, copy that block's contents to the spare block and redirect appropriate interrupt vectors to point to that block. After update is complete, redirect interrupt vectors back to the original block, erase the spare block and move to the next block to be updated. This approach will obviously "cycle" block 31 more than any of the others, but this is often acceptable if the number of expected code updates through system lifetime is not excessive.

If spare blocks are not available or expected updates are numerous, copy block information to RAM before updating. This approach requires dedicated RAM for this function but needs much less RAM than a technique like Technique 4.1, where the entire flash memory array is shadowed.

Putting It All Together

Referring back to our example scenario in Figure 9, we conclude with the following summary.

Component block 0 is locked and stores system boot code and the flash memory update routine. The interrupt vector table, stored in an unlocked block to enable its revision, is copied from flash memory to RAM on system power-up. During flash memory update, interrupt vector table contents point to the flash memory update routine, also copied to RAM. When an interrupt occurs, this routine determines via a bit "flag" if block erase is in progress and if so, suspends erase before jumping to the necessary interrupt service code. After servicing the interrupt, the update routine resumes erase or executes location programming operations, depending on where in the update the interrupt occurred.

Ideally, to minimize system overhead and maximize effective update throughput, the update algorithm should be present in RAM at all times during system operation. If this is not possible due to "RAM crunch," the up-front time required to upload the algorithm to RAM must be factored into system update performance calculations.

Before erasing and reprogramming a flash memory block, system software copies block contents to the spare block and appropriately redirects the interrupt vector table. After block erase/reprogram completes, the update routine redirects interrupts back to the block, erases the spare block and moves to the next block to be updated.

Program/Erase Suspend Performance, Typical/Max vs. Cycling

Depending on how "tight" the timings are using the equations of Technique 4.3 with your specifications, and depending on the expected flash memory update frequency (cycling) through system lifetime, additional information may be needed to determine whether this technique is applicable to your design. In this case, please contact your local Intel or distribution sales office for additional information on typical/max program, erase and erase suspend specifications as a function of cycling for the Intel flash memory of interest.

What If Interrupt Period Is too Short or Interrupt Latency Is too Long?

Technique 4.3 assumes that system interrupt timings allowed sufficient time for erase suspend and byte/word programming. If at first inspection this does not seem to be the case for your design, answer the following questions in the process of further analyzing your system interrupt profile:

- Do interrupts occur fairly regularly as a function of time, or in bursts of activity followed by periods of "quiet?" If the latter, your system software can hold off attempting location programming or resuming erase until it detects a specified time span of system "inactivity."
- Do one or several interrupt service routines have substantially longer latencies than others? If so, system software can hold off attempting programming or initiating/resuming erase when these specific interrupts occur.

In some cases, it may be difficult to hold off programming due to a fixed data write transfer rate to the flash memory subsystem. In these cases, a small RAM FIFO can potentially be integrated within the interface logic (ASIC, FPGA, etc.). This FIFO acts as a buffer between system and flash memory and accommodates programming delays due to interrupt bursts or long ISR latencies.

As an alternative, the approaches described in Techniques 4.1 and 4.2 can be reviewed to determine applicability with your system design criteria.

Programming (Writing) during Erase

Some system designs require both the ability to quickly read code from flash memory and to quickly write information to flash memory in response to an interrupt. Intel's 16-Mbit FlashFile memories offer enhanced on-chip automation that, among its features, automatically suspends block erase to service queued programming operations to other blocks.

5.0 CONCLUSION

Intel has developed a wide range of documentation and other collateral to assist you in developing system software solutions and profiling cycling through system lifetime. Please contact your local Intel or Distribution Sales Office for more information on Intel's flash memory products.

6.0 ADDITIONAL INFORMATION

Documentation

Device datasheets provide in-depth information on device operating modes and specifications.

The 16-Mbit Flash Product Family User's Manual (order #297372) gives detailed information on the enhanced automation of Intel's 16-/32-Mbit FlashFile and Embedded Flash RAM memories. Included flowcharts assist you in developing system software.

The following application notes deal specifically with software interfacing to Intel flash memories:

Order Number	Document
292046	AP-316 "Using Flash Memory for In-System Reprogrammable Nonvolatile Storage"
292059	AP-325 "Guide to First Generation Flash Memory Reprogramming"
292077	AP-341 "Designing an Updateable BIOS Using Flash Memory"
292095	AP-360 "28F008SA Software Drivers"
292099	AP-364 "28F008SA Automation and Algorithms"
292148	AP-604 "Using Intel's Boot Block Flash Memory Parameter Blocks to Replace EEPROM"
292126	AP-377 "16-Mbit Flash Product Family Software Drivers"

NOTES:

Please call the Intel Literature Center at 1-800-548-4725 to request Intel documentation. International customers should contact their local Intel or distribution sales office.

Additional information can be requested from Intel's automated FaxBACK* system at 1-800-628-2283 or 916-356-3105 (+44(0)793-496646 in Europe).

FLASHBuilder

This Windows-based utility is a hypertext aid to understanding the automation of Intel's 16-Mbit FlashFile and Embedded Flash RAM memories. FLASHBuilder automatically generates code segments in C or ASM-86 for flash memory program/erase that you can easily "paste" into your system software. It also includes a cycling utility and power/performance benchmark utilities for the 28F016XS and 28F016XD.

FLASHBuilder is available from the Intel Literature Center via order number #297508. It can also be downloaded from the Intel BBS at 916-356-3600 (+44(0)793-49-6340 in Europe).

VHDL and Verilog Models

VHDL functional simulation models for the 28F016SV, 28F016XD and 28F016XS are available now; please contact your local Intel or distribution sales office. Verilog models for these devices will be available in early 1995.

PROM Programming Support

Intel works closely with a large number of world-wide PROM programmer vendors to ensure timely support for its flash memory products. This programming support information, updated frequently, is available on FaxBACK.

On-Board Programming

An application note will be available in early 1995 that discusses hardware and software recommendations for OBP using either a board tester or PROM programmer. Contact your local Intel or distribution sales office for more details.

REVISION HISTORY

Number	Description
001	Original Version
002	Removed page buffer references for Embedded Flash RAM memories

NORTH AMERICAN SALES OFFICES

ALABAMA

Intel Corp.
4024 Medford Drive
Huntsville 35802
Tel: (205) 883-6137
FAX: (205) 883-4826

ARIZONA

†Intel Corp.
410 North 44th Street
Suite 500
Phoenix 85008
Tel: (800) 628-8686
FAX: (602) 244-0446

CALIFORNIA

Intel Corp.
3550 Watt Avenue
Suite 140
Sacramento 95821
Tel: (800) 628-8686
FAX: (916) 488-1473

†Intel Corp.
9655 Granite Ridge Drive
3rd Floor, Suite 4A
San Diego 92123
Tel: (800) 628-8686
FAX: (619) 467-2460

Intel Corp.
1781 Fox Drive
San Jose 95131
Tel: (800) 628-8686
FAX: (408) 441-9540

*†Intel Corp.
1551 N. Tustin Avenue
Suite 800
Santa Ana 92701
Tel: (800) 628-8686
TWX: 910-595-1114
FAX: (714) 541-9157

†Intel Corp.
15260 Ventura Boulevard
Suite 360
Sherman Oaks 91403
Tel: (800) 628-8686
FAX: (818) 995-6624

Intel Corp.
120 Birmingham
Suite 110-114
Cardiff, CA 92007
Tel: (619) 942-8938
FAX: (619) 942-2849

Intel Corp.
300 N. Continental Blvd.
Suite 100
El Segundo 90245
Tel: (800) 628-8686
FAX: (310) 640-7133

COLORADO

*†Intel Corp.
600 S. Cherry St.
Suite 700
Denver 80222
Tel: (800) 628-8686
TWX: 910-931-2289
FAX: (303) 322-8670

CONNECTICUT

†Intel Corp.
40 Old Ridgebury Road
Suite 311
Danbury 06877
Tel: (800) 628-8686
FAX: (203) 778-2168

FLORIDA

†Intel Corp.
800 Fairway Drive
Suite 160
Deerfield Beach 33441
Tel: (800) 628-8686
FAX: (305) 421-2444

Intel Corp.
2250 Lucien Way
Suite 100, Room 8
Maitland 32751
Tel: (800) 628-8686
FAX: (407) 660-1283

GEORGIA

†Intel Corp.
20 Technology Park
Suite 150
Norcross 30092
Tel: (800) 628-8686
FAX: (404) 448-0875

IDAHO

Intel Corp.
9456 Fairview Ave., Suite C
Boise 83704
Tel: (800) 628-8686
FAX: (208) 377-1052

ILLINOIS

*†Intel Corp.
Woodfield Corp. Center III
300 N. Martingale Road
Suite 400
Schaumburg 60173
Tell: (800) 628-8686
FAX: (708) 605-9762

INDIANA

†Intel Corp.
8041 Knue Road
Indianapolis 46250
Tel: (800) 628-8686
FAX: (317) 577-4939

MARYLAND

*†Intel Corp.
131 National Business Parkway
Suite 200
Annapolis Junction 20701
Tel: (800) 628-8686
FAX: (301) 206-3678

MASSACHUSETTS

*†Intel Corp.
Westford Corp. Center
5 Carlisle Road
2nd Floor
Westford 01886
Tel: (800) 628-8686
TWX: 710-343-6333
FAX: (508) 692-7867

MICHIGAN

†Intel Corp.
7071 Orchard Lake Road
Suite 100
West Bloomfield 48322
Tel: (800) 628-8686
FAX: (313) 851-8770

Intel Corp.
32255 N. Western Hwy.
Suite 212, Tri Atria
Farmington Hills 48334
Tel: (800) 628-8686
FAX: (313) 851-8770

MINNESOTA

†Intel Corp.
3500 W. 80th St.
Suite 360
Bloomington 55431
Tel: (800) 628-8686
TWX: 910-576-2867
FAX: (612) 831-6497

NEW JERSEY

Intel Corp.
2001 Route 46, Suite 310
Parsippany 07054-1315
Tel: (800) 628-8686
FAX: (201) 402-4893

*†Intel Corp.
Lincroft Center
125 Half Mile Road
Red Bank 07701
Tel: (800) 628-8686
FAX: (908) 747-0983

NEW YORK

*Intel Corp.
850 Cross Keys Office Park
Fairport 14450
Tel: (800) 628-8686
TWX: 510-253-7391
FAX: (716) 223-2561

*†Intel Corp.
2950 Express Dr. South
Suite 130
Islandia 11722
Tel: (800) 628-8686
TWX: 510-227-6236
FAX: (516) 348-7939

OHIO

*Intel Corp.
56 Milford Dr., Suite 205
Hudson 44236
Tel: (800) 628-8686
FAX: (216) 528-1026

*†Intel Corp.
3401 Park Center Drive
Suite 220
Dayton 45414
Tel: (800) 628-8686
TWX: 810-450-2528
FAX: (513) 890-8658

OKLAHOMA

Intel Corp.
6801 N. Broadway
Suite 115
Oklahoma City 73162
Tel: (800) 628-8686
FAX: (405) 840-9819

OREGON

†Intel Corp.
15254 NW Greenbrier Pkwy.
Building B
Beaverton 97006
Tel: (800) 628-8686
TWX: 910-467-8741
FAX: (503) 645-8181

PENNSYLVANIA

*†Intel Corp.
925 Harvest Drive
Suite 200
Blue Bell 19422
Tel: (800) 628-8686
FAX: (215) 641-0785

SOUTH CAROLINA

Intel Corp.
7403 Parklane Rd., Suite 4
Columbia 29223
Tel: (800) 628-8686
FAX: (803) 788-7999

Intel Corp.
100 Executive Center Drive
Suite 109, B183
Greenville 29615
Tel: (800) 628-8686
FAX: (803) 297-3401

TEXAS

†Intel Corp.
8911 N. Capital of Texas Hwy.
Suite 4230
Austin 78759
Tel: (800) 628-8686
FAX: (512) 338-9335

*†Intel Corp.
5000 Quorum Drive
Suite 750
Dallas 75240
Tel: (800) 628-8686
FAX: (214) 233-1325

*†Intel Corp.
20515 SH 249
Suite 401
Houston 77070
Tel: (800) 628-8686
TWX: 910-881-2490
FAX: (713) 376-2891

UTAH

†Intel Corp.
428 East 6400 South
Suite 135
Murray 84107
Tel: (800) 628-8686
FAX: (801) 268-1457

Intel Corp.
2581 E. Cobblestone Way
Sandy, UT 84093
Tel: (801) 942-8820
FAX: (801) 942-8815

WASHINGTON

†Intel Corp.
2800 156th Avenue SE
Suite 105
Bellevue 98007
Tel: (800) 628-8686
FAX: (206) 746-4495

WISCONSIN

Intel Corp.
400 N. Executive Dr.
Suite 401
Brookfield 53005
Tel: (800) 628-8686
FAX: (414) 789-2746

CANADA

BRITISH COLUMBIA

Intel Semiconductor of
Canada, Ltd.
999 Canada Place
Suite 404, #11
Vancouver V6C 3E2
Tel: (800) 628-8686
FAX: (604) 844-2813

ONTARIO

†Intel Semiconductor of
Canada, Ltd.
2650 Queensview Drive
Suite 250
Ottawa K2B 8H6
Tel: (800) 628-8686
FAX: (613) 820-5936

†Intel Semiconductor of
Canada, Ltd.
190 Attwell Drive
Suite 500
Rexdale M9W 6H8
Tel: (800) 628-8686
FAX: (416) 675-2438

QUEBEC

†Intel Semiconductor of
Canada, Ltd.
1 Rue Holiday, Tour West
Suite 320
Pt. Claire H9R 5N3
Tel: (800) 628-8686
FAX: 514-694-0064

†Sales and Service Office
*Field Application Location

intel®

UNITED STATES, Intel Corporation
2200 Mission College Blvd., P.O. Box 58119, Santa Clara, CA 95052-8119
Tel: (408) 765-8080

JAPAN, Intel Japan K.K.
5-6 Tokodai, Tsukuba-shi, Ibaraki-ken 300-26
Tel: 0298-47-8511

FRANCE, Intel Corporation S.A.R.L.
1, Rue Edison, BP 303, 78054 Saint-Quentin-en-Yvelines Cedex
Tel: (33) (1) 30 57 70 00

UNITED KINGDOM, Intel Corporation (U.K.) Ltd.
Pipers Way, Swindon, Wiltshire, England SN3 1RJ
Tel: (44) (0793) 696000

GERMANY, Intel GmbH
Dornacher Strasse 1
8016 Feldkirchen bei Muenchen
Tel: (49) 089/90992-0

HONG KONG, Intel Semiconductor Ltd.
32/F Two Pacific Place, 88 Queensway, Central
Tel: (852) 844-4555

CANADA, Intel Semiconductor of Canada, Ltd.
190 Attwell Drive, Suite 500
Rexdale, Ontario M9W 6H8
Tel: (416) 675-2105

Printed in USA/0395/7.5K/MS TS
Memory Products